INFORMATION DISCLOSURE STATEMENT

Applicant	:	Arthur Sherman
App. No.	:	Unknown
Filed	:	Herewith
For	:	SEQUENTIAL CHEMICAL VAPOR DEPOSITION
Examiner	:	Unknown
Group Art Unit	:	Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing two hundred forty-three (243) references that were previously disclosed to or cited by the Patent and Trademark Office in the prosecution of U.S. patent application No. 09/866,156, filed May 24, 2001, which is the parent of this application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d). This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 10, 2003

By: _____

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Attorney of Record
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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMMC.9CP1DV1C1	APPLICATION NO. To be assigned
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	2.	4,282,267	08/04/81	Küyel			
	3.	4,389,973	06/28/83	Suntola et al.	118	725	12/11/81
	4.	4,747,367	05/31/88	Posa			
	5.	4,761,269	08/02/88	Conger et al.			
	6.	4,767,494	08/30/88	Kobayashi	156	606	09/19/86
	7.	4,845,049	07/04/89	Sunakawa	437	81	03/28/88
	8.	4,851,095	07/89	Scobey et al.			
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	10.	4,876,218	10/24/89	Pessa et al.	437	107	09/26/88
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	50.	6,203,613	03/20/01	Gates et al.	117	104	10/19/99
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	52.	6,342,277	01/2002	Sherman			
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
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	55.	0 442 490 A1	21.08.91	Europe				
	56.	0 526 779 A1	10.02.93	Europe				
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